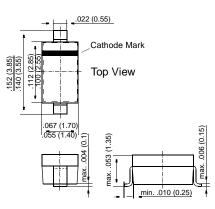
BA782, BA783

Bandswitching Diodes

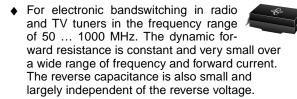
FEATURES

<u>SOD-123</u>



Dimensions in inches and (millimeters)

• Silicon Epitaxial Planar Diode Switches



 These diodes are also available in SOD-323 case with the type designations BA782S and BA783S.

MECHANICAL DATA

Case: SOD-123 Plastic Case Weight: approx. 0.01 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

| | Symbol | Value | Unit |
|--|----------------|-------------|------|
| Reverse Voltage | V _R | 35 | V |
| Forward Continuous Current at T _{amb} = 25 °C | ١ _F | 100 | mA |
| Junction Temperature | Tj | 125 | °C |
| Storage Temperature Range | T _S | -55 to +125 | °C |



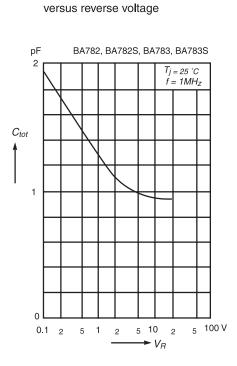
BA782, BA783

ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

| | | Symbol | Min. | Тур. | Max. | Unit |
|---|----------------------------------|--|------------------|-------------|--------------------------|------------------|
| Forward Voltage at I _F = 100 mA | | V _F | - | - | 1 | V |
| Leakage Current at V _R = 20 V | | I _R | - | - | 50 | nA |
| Dynamic Forward Resistance at f = 50 to 1000 MHz, $I_F = 3 \text{ mA}$ at f = 50 to 1000 MHz, $I_F = 10 \text{ mA}$ | BA782 BA783 BA782 BA783 | r _f r _f r _f r _f | - - - - | | 0.7 1.2 0.5 0.9 | Ω Ω Ω Ω |
| Capacitance at $V_R = 1$ V, f = 1 MHz at $V_R = 3$ V, f = 1 MHz | BA782 BA783 | C _{tot} C _{tot} C _{tot} | | _ _ _ | 1.5 1.25 1.2 | pF pF pF |
| Series Inductance across Case | | L _S | - | 2.5 | - | nH |

RATINGS AND CHARACTERISTIC CURVES BA782, BA783



Capacitance

Dynamic forward resistance versus forward voltage

